

NTR4170N

MOSFET – Power, Single, N-Channel, SOT-23

30 V, 3.1 A

Features

- Low $R_{DS(on)}$
- Low Gate Charge
- Low Threshold Voltage
- Halide Free
- This is a Pb-Free Device

Applications

- Power Converters for Portables
- Battery Management
- Load/Power Switch

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit		
Drain-to-Source Voltage	V_{DSS}	30	V		
Gate-to-Source Voltage	V_{GS}	± 12	V		
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	2.4	A	
			$t \leq 30$ s		3.1
			$t \leq 10$ s		3.9
	Steady State	$T_A = 85^\circ\text{C}$	1.7		
			$t \leq 30$ s		2.3
			$t \leq 10$ s		2.8
Power Dissipation (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	P_D	0.48	W
			$t \leq 30$ s	0.82	
			$t \leq 10$ s	P_D	1.25
Pulsed Drain Current	$t_p = 10 \mu\text{s}$	I_{DM}	8.0	A	
Operating Junction and Storage Temperature	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$		
Source Current (Body Diode)	I_S	0.82	A		
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$		

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	260	$^\circ\text{C}/\text{W}$
Junction-to-Ambient – $t \leq 30$ s	$R_{\theta JA}$	153	
Junction-to-Ambient – $t < 10$ s (Note 1)	$R_{\theta JA}$	100	

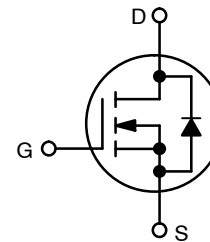


ON Semiconductor®

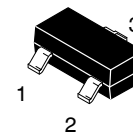
www.onsemi.com

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
30 V	55 m Ω @ 10 V	3.1 A
	70 m Ω @ 4.5 V	2.8 A
	110 m Ω @ 2.5 V	2.0 A

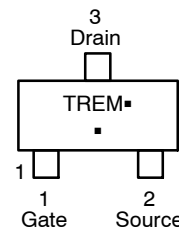
SIMPLIFIED SCHEMATIC – N-CHANNEL



MARKING DIAGRAM/ PIN ASSIGNMENT



SOT-23
CASE 318
STYLE 21



TRE = Specific Device Code

M = Date Code

▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NTR4170NT1G	SOT-23 (Pb-Free)	3000/Tape & Reel
NTR4170NT3G	SOT-23 (Pb-Free)	10000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NTR4170N

1. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).

NTR4170N

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} / T _J	I _D = 250 μA, Reference to 25°C		26.4		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 24 V, T _J = 25°C V _{GS} = 0 V, V _{DS} = 24 V, T _J = 125°C			1.0 5.0	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±12 V			±100	nA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	0.6	1.0	1.4	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} / T _J			3.3		mV/°C
Drain-to-Source On-Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 3.2 A		45	55	mΩ
		V _{GS} = 4.5 V, I _D = 2.8 A		50	70	
		V _{GS} = 2.5 V, I _D = 2.0 A		64	110	
Forward Transconductance	g _{FS}	V _{DS} = 5.0 V, I _D = 3.2 A		8.0		S

CHARGES, CAPACITANCES AND GATE RESISTANCE

Input Capacitance	C _{iss}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 15 V		432		pF
Output Capacitance	C _{oss}			53.6		
Reverse Transfer Capacitance	C _{rss}			37.1		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 15 V, I _D = 3.2 A		4.76		nC
Threshold Gate Charge	Q _{G(TH)}			0.3		
Gate-to-Source Charge	Q _{GS}			1.0		
Gate-to-Drain Charge	Q _{GD}			1.4		
Gate Resistance	R _G			3.8		Ω

SWITCHING CHARACTERISTICS, V_{GS} = 4.5 V (Note 4)

Turn-On Delay Time	t _{d(on)}	V _{GS} = 4.5 V, V _{DD} = 15 V, I _D = 3.2 A, R _G = 6.2 Ω		6.4		ns
Rise Time	t _r			9.9		
Turn-Off Delay Time	t _{d(off)}			15.1		
Fall Time	t _f			3.5		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 1.0 A, T _J = 25°C		0.75	1.0	V
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, I _S = 1.0 A, dI _{SD} /dt = 100 A/μs		8.0		ns
Charge Time	t _a			5.1		
Discharge Time	t _b			2.9		
Reverse Recovery Charge	Q _{RR}			2.9		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Surface-mounted on FR4 board using 1 in sq pad size (CU area = 1.127 in sq [2 oz] including traces).
- Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
- Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

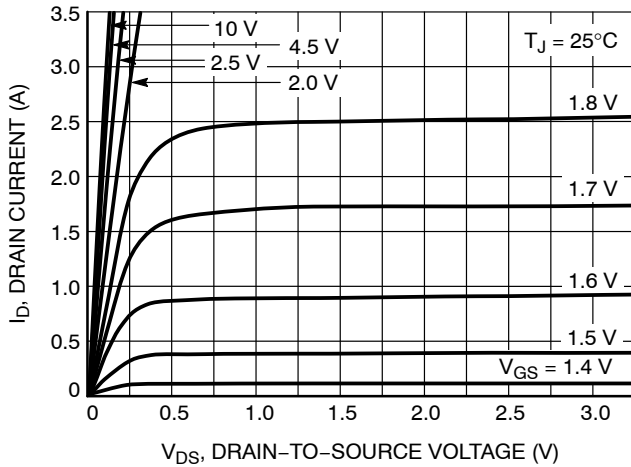


Figure 1. On-Region Characteristics

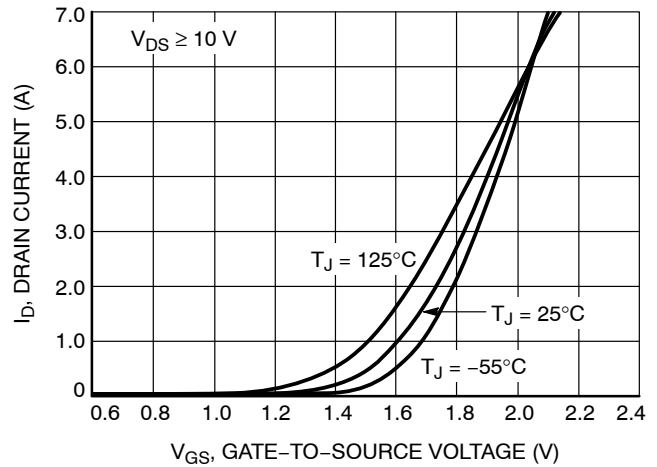


Figure 2. Transfer Characteristics

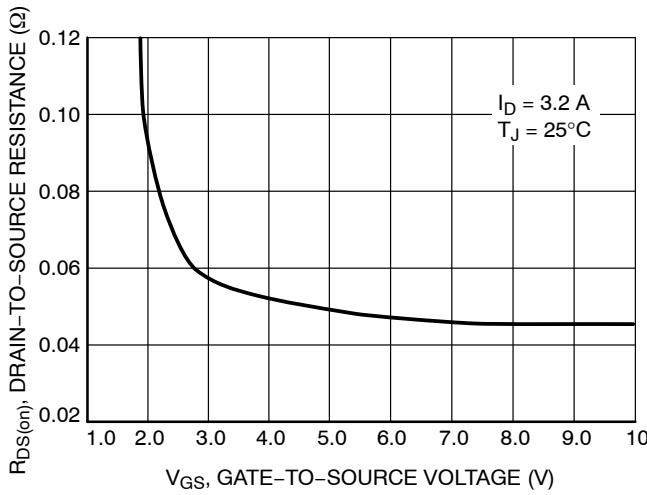


Figure 3. On-Resistance vs. Gate Voltage

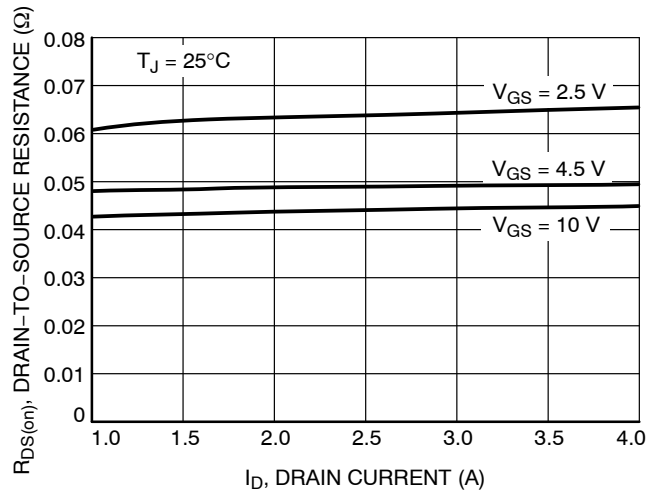


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

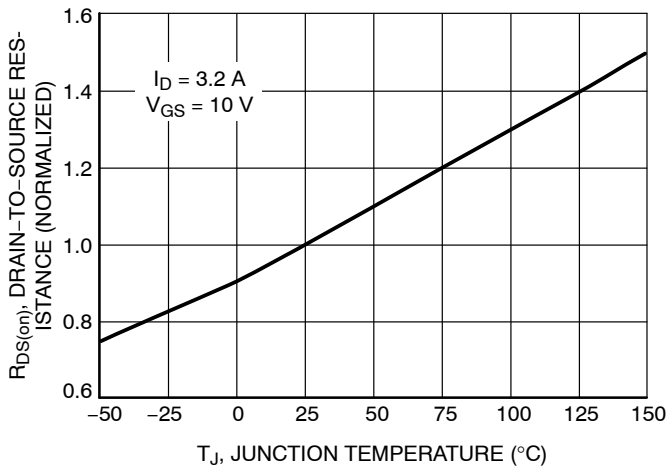


Figure 5. On-Resistance Variation with Temperature

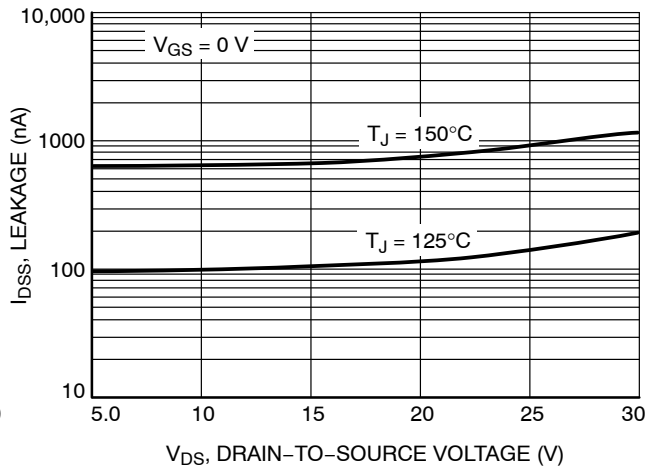


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

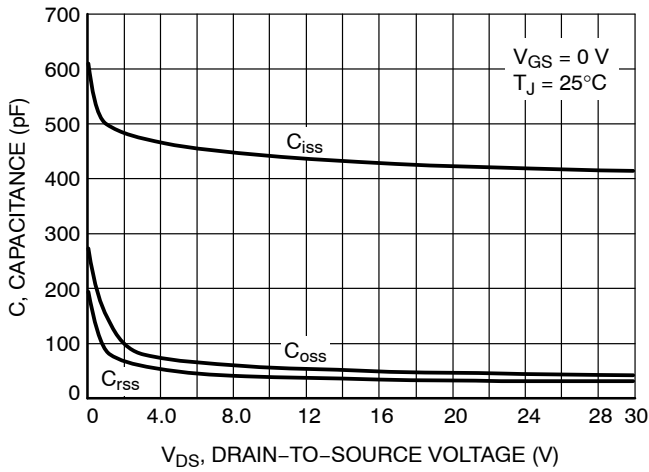


Figure 7. Capacitance Variation

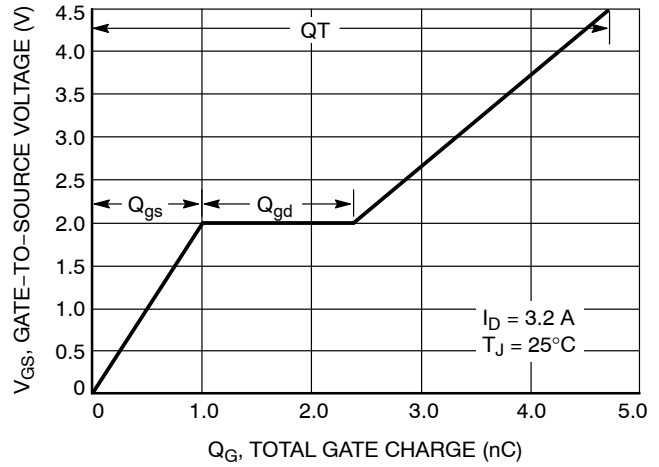


Figure 8. Gate-to-Source Voltage vs. Total Charge

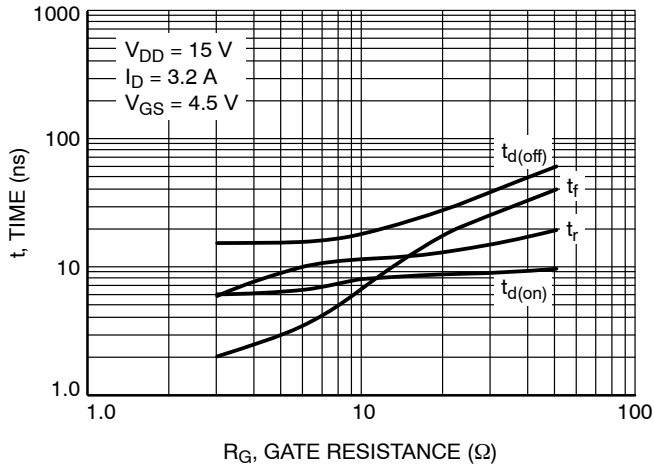


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

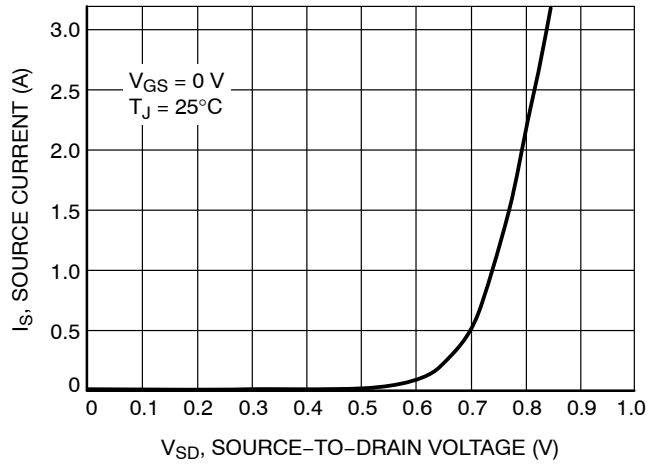


Figure 10. Diode Forward Voltage vs. Current

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SOT-23 (TO-236)
CASE 318
ISSUE AT

DATE 01 MAR 2023

SCALE 4:1



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H _E	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

GENERIC MARKING DIAGRAM*



- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOT-23 (TO-236)	PAGE 1 OF 2

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS



SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOT-23 (TO-236)	PAGE 2 OF 2

onsemi and **ONSEMI** are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales



单击下面可查看定价，库存，交付和生命周期等信息

[>>ON Semiconductor\(安森美\)](#)